

Notice of References Cited	Application/Control No. 10/668,974		Applicant(s)/Patent Under Reexamination SHIMIZU ET AL.	
	Examiner Mary C. Jacob		Art Unit 2123	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-6,909,976	06-2005	Kitamaru et al.	702/64
*	C	US-6,314,390	11-2001	Bittner et al.	703/14
*	D	US-6,618,837	09-2003	Zhang et al.	716/4
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	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

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	U	Chung et al, "An Analytical Threshold-Voltage Model of Trench-Isolated MOS Devices with Nonuniformly Doped Substrates", IEEE Transactions on Electron Devices, Vol. 39, No. 3, March 1992
	V	Lin et al, "A Closed-Form Back-Gate-Bias Related Inverse Narrow-Channel Effect Model for Seep-Submicron VLSI CMOS Devices Using Shallow Trench Isolation", IEEE Transactions on Electron Devices, Vol. 47, No. 4, April 2000
	W	Bianchi et al, "Accurate Modeling of Trench Isolation Induced Mechanical Stress Effects on MOSFET Electrical Performance", International Electron Devices Meeting, IDEM '02, Digest, pages 117-120, December 8-11, 2002
	X	Yamaguchi, Ken, "Field Dependent Mobility Model for Two-Dimensional Numerical Analysis of MOSFET's", IEEE Transactions on Electron Devices, Vol. ED-26, No. 7, July, 1979

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.